













## OPA209, OPA2209, OPA4209

SBOS426D - NOVEMBER 2008-REVISED OCTOBER 2016

# OPAx209 2.2-nV/ $\sqrt{\text{Hz}}$ , Low-Power, 36-V Operational Amplifier

## **Features**

Low Voltage Noise: 2.2 nV/√Hz at 1 kHz

0.1-Hz to 10-Hz Noise: 130 nV<sub>PP</sub>

Low Quiescent Current: 2.5 mA/Ch (Maximum)

Low Offset Voltage: 150 µV (Maximum)

Gain Bandwidth Product: 18 MHz

Slew Rate: 6.4 V/µs Wide Supply Range:

±2.25 V to ±18 V, 4.5 V to 36 V

Rail-to-Rail Output

Short-Circuit Current: ±65 mA

Available in 5-Pin SOT-23, 8-Pin MSOP, 8-Pin SOIC, and 14-Pin TSSOP Packages

## 2 Applications

- PLL Loop Filters
- Low-Noise, Low-Power Signal Processing
- Low-Noise Instrumentation Amplifiers
- High-Performance ADC Drivers
- High-Performance DAC Output Amplifiers
- Active Filters
- **Ultrasound Amplifiers**
- **Professional Audio Preamplifiers**
- Low-Noise Frequency Synthesizers
- Infrared Detector Amplifiers
- **Hydrophone Amplifiers**

## 3 Description

OPA209 series of precision operational amplifiers achieve very low voltage noise density (2.2 nV/√Hz) with a supply current of only 2.5 mA (maximum). This series also offers rail-to-rail output swing, which helps to maximize dynamic range.

In precision data acquisition applications, the OPA209 provides fast settling time to 16-bit accuracy, even for 10-V output swings. This excellent ac performance, combined with only 150 µV (maximum) of offset and low drift over temperature, makes the OPA209 very suitable for fast, high-precision applications.

The OPA209 is specified over a wide dual powersupply range of ±2.25 V to ±18 V, or single-supply operation from 4.5 V to 36 V.

The OPA209 is available in the 5-pin SOT-23, 8-pin VSSOP, and the standard 8-pin SOIC packages. The dual OPA2209 comes in both 8-pin VSSOP and 8-pin SOIC packages. The quad OPA4209 is available in the 14-pin TSSOP package.

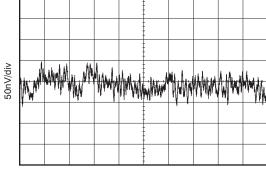
The OPA209 series is specified from -40°C to 125°C.

## Device Information<sup>(1)</sup>

PART NUMBER	PACKAGE	BODY SIZE (NOM)
	SOT-23 (5)	2.90 mm × 1.60 mm
OPA209	VSSOP (8)	3.00 mm × 3.00 mm
	SOIC (8)	4.90 mm × 3.91 mm
OPA2209	VSSOP (8)	3.00 mm × 3.00 mm
OPA2209	SOIC (8)	4.90 mm × 3.91 mm
OPA4209	TSSOP (14)	5.00 mm × 4.40 mm

<sup>(1)</sup> For all available packages, see the orderable addendum at the end of the data sheet.

## 0.1-Hz to 10-Hz Noise



Time (1s/div)



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## 4 Revision History

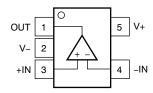
NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Ch	nanges from Revision C (October 2013) to Revision D	Page
•	Added ESD Ratings table, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and Mechanical, Packaging, and Orderable Information section	
•	Deleted Ordering Information table; see POA at the end of the data sheet	1
•	Moved specified voltage, specified temperature, and operating temperature from <i>Electrical Characteristics</i> to <i>Recommended Operating Conditions</i>	5
<u>.</u>	Updated values in the Thermal Information tables to align with JEDEC standards	5
Cr	nanges from Revision B (August 2010) to Revision C	Page
•	Deleted device graphic	1
•	Changed y-axis units label in Figure 2	8

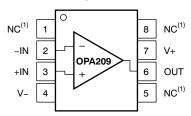


# 5 Pin Configuration and Functions

#### OPA209: DBV Package 5-Pin SOT-23 Top View



#### OPA209: D or DGK Packages 8-Pin SOIC or VSSOP Top View

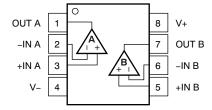


(1) NC = no internal connection

## **Pin Functions: OPA209**

	PIN		1/0	DESCRIPTION	
NAME	SOT-23	SOIC, VSSOP	1/0	DESCRIPTION	
-IN	4	2	I	Inverting input	
+IN	3	3	I	Noninverting input	
NC	_	1, 5, 8	_	No internal connection	
OUT	1	6	0	Output	
V-	2	4	_	Negative (lowest) power supply	
V+	5	7	_	Positive (highest) power supply	

#### OPA2209: D or DGK Packages 8-Pin SOIC or VSSOP Top View



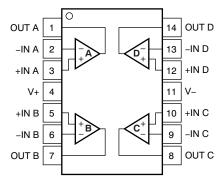
## **Pin Functions: OPA2209**

PIN		1/0	DESCRIPTION
NAME	NO.	1/0	DESCRIPTION
–IN A	2	I	Inverting input, channel A
+IN A	3	I	Noninverting input, channel A
–IN B	6	I	Inverting input, channel B
+IN B	5	I	Noninverting input, channel B
OUT A	1	0	Output, channel A
OUT B	7	0	Output, channel B
V-	4	_	Negative (lowest) power supply
V+	8	_	Positive (highest) power supply

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#### OPA4209: PW Package 14-Pin TSSOP Top View



## Pin Functions: OPA4209

PIN I/O		1/0	DESCRIPTION
NAME	NO.	1/0	DESCRIPTION
−IN A	2	1	Inverting input, channel A
+IN A	3	1	Noninverting input, channel A
–IN B	6	I	Inverting input, channel B
+IN B	5	I	Noninverting input, channel B
-IN C	9	I	Inverting input, channel C
+IN C	10	I	Noninverting input, channel C
–IN D	13	1	Inverting input, channel D
+IN D	12	1	Noninverting input, channel D
OUT A	1	0	Output, channel A
OUT B	7	0	Output, channel B
OUT C	8	0	Output, channel C
OUT D	14	0	Output, channel D
V-	11	_	Negative (lowest) power supply
V+	4	_	Positive (highest) power supply



## 6 Specifications

## 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

		MIN	MAX	UNIT
Voltage	Supply voltage, $V_S = (V+) - (V-)$		40	V
	Signal input pins (2)	(V-) - 0.5	(V+) + 0.5	V
Comment	Signal input pins (2)	-10	10	mA
Current	Output short circuit (3)	Continuous		
	Operating, T <sub>A</sub>	-55	150	°C
Temperature	Junction, T <sub>J</sub>		200	°C
	Storage, T <sub>stg</sub>	-65	150	°C

<sup>(1)</sup> Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

## 6.2 ESD Ratings

			VALUE	UNIT
.,		Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)	±3000	
V <sub>(ESD)</sub>	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 <sup>(2)</sup>	±1000	V

<sup>(1)</sup> JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

## 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
Vs	Specified voltage	±2.25	±18	V
	Specified temperature	-40	125	°C
T <sub>A</sub>	Operating temperature	<b>-</b> 55	150	°C

#### 6.4 Thermal Information: OPA209

	THERMAL METRIC <sup>(1)</sup>	DBV (SOT-23)	D (SOIC)	DGK (VSSOP)	UNIT
		5 PINS	8 PINS	8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	204.9	135.5	142.6	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	200	73.7	46.9	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	113.1	61.9	63.5	°C/W
ΨЈТ	Junction-to-top characterization parameter	38.2	19.7	5.3	°C/W
ΨЈВ	Junction-to-board characterization parameter	104.9	54.8	62.8	°C/W

For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

Product Folder Links: OPA209 OPA2209 OPA4209

<sup>2)</sup> For input voltages beyond the power-supply rails, voltage or current must be limited.

<sup>(3)</sup> Short-circuit to ground, one amplifier per package.

<sup>(2)</sup> JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



#### 6.5 Thermal Information: OPA2209

		OP	OPA2209		
	THERMAL METRIC <sup>(1)</sup>	D (SOIC)	DGK (VSSOP)	UNIT	
		8 PINS	8 PINS		
$R_{\theta JA}$	Junction-to-ambient thermal resistance	134.3	132.7	°C/W	
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	72.1	38.5	°C/W	
$R_{\theta JB}$	Junction-to-board thermal resistance	60.7	52.1	°C/W	
ΨЈΤ	Junction-to-top characterization parameter	18.2	2.4	°C/W	
ΨЈВ	Junction-to-board characterization parameter	53.8	52.8	°C/W	

<sup>(1)</sup> For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

## 6.6 Thermal Information: OPA4209

		OPA4209		
	THERMAL METRIC <sup>(1)</sup>	PW (TSSOP)	UNIT	
		14 PINS		
$R_{\theta JA}$	Junction-to-ambient thermal resistance	112.9	°C/W	
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	26.1	°C/W	
$R_{\theta JB}$	Junction-to-board thermal resistance	61	°C/W	
ΤιΨ	Junction-to-top characterization parameter	0.7	°C/W	
ΨЈВ	Junction-to-board characterization parameter	59.2	°C/W	

<sup>(1)</sup> For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

## 6.7 Electrical Characteristics

at  $V_S = \pm 2.25$  V to  $\pm 18$  V,  $T_A = 25$ °C,  $R_L = 10$  k $\Omega$  connected to midsupply, and  $V_{CM} = V_{OUT} =$  midsupply (unless otherwise noted)

	PARAMETER	TEST CO	ONDITIONS	MIN	TYP	MAX	UNIT		
OFFSET	VOLTAGE			•		•			
V <sub>OS</sub>	Input offset voltage	$V_S = \pm 15 \text{ V}, V_{CM} = 0 \text{ V}$			±35	±150	μV		
dV <sub>OS</sub> /dT	Input offset voltage drift	$T_A = -40^{\circ}C$ to 125°C			1	3	μV/°C		
DODD		V .005 V 45 .40 V	T <sub>A</sub> = 25°C		0.05	0.5	\/\/		
PSRR	vs power supply	$V_S = \pm 2.25 \text{ V to } \pm 18 \text{ V}$	$T_A = -40^{\circ}\text{C} \text{ to } 125^{\circ}\text{C}$			1	μV/V		
	Channel separation	DC (dual and quad versions)			1		μV/V		
INPUT BI	AS CURRENT								
			T <sub>A</sub> = 25°C	±1		±4.5			
l <sub>B</sub>	l <sub>B</sub> Input bias current	V <sub>CM</sub> = 0 V	$T_A = -40$ °C to 85°C			±8	nA		
			$T_A = -40^{\circ}\text{C} \text{ to } 125^{\circ}\text{C}$			±15	ĺ		
I <sub>OS</sub> Input offset current	V <sub>CM</sub> = 0 V	T <sub>A</sub> = 25°C		±0.7	±4.5				
		$T_A = -40$ °C to 85°C			±8	nA			
			$T_A = -40^{\circ}\text{C} \text{ to } 125^{\circ}\text{C}$			±15			
NOISE			·						
e <sub>n</sub>	Input voltage noise	f = 0.1 Hz to 10 Hz			0.13		$\mu V_{PP}$		
		f = 10 Hz			3.3				
	Noise density	f = 100 Hz		2.25			nV/√Hz		
		f = 1 kHz			2.2				
In	Input current noise density	f = 1 kHz			500		fA/√Hz		
INPUT VC	DLTAGE RANGE								
V <sub>CM</sub>	Common-mode voltage range			(V-) + 1.5		(V+) - 1.5	V		
CMRR	Common-mode rejection ratio	(V–) + 1.5 V < V <sub>CM</sub> < (V+) – 1	1.5 V, T <sub>A</sub> = -40°C to 125°C	120	130		dB		

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## **Electrical Characteristics (continued)**

at  $V_S$  = ±2.25 V to ±18 V,  $T_A$  = 25°C,  $R_L$  = 10 k $\Omega$  connected to midsupply, and  $V_{CM}$  =  $V_{OUT}$  = midsupply (unless otherwise

	PARAMETER	TEST CONDI	TIONS	MIN	TYP	MAX	UNIT
INPUT IMI	PEDANCE						
	Differential				200    4		kΩ    pF
	Common-mode				10 <sup>9</sup>    2		Ω    pF
OPEN-LO	OP GAIN						
		$(V-) + 0.2 V < V_O < (V+) - 0.2 V,$	T <sub>A</sub> = 25°C	126	132		
٨	Open-loop voltage gain	$R_L = 10 \text{ k}\Omega$	$T_A = -40$ °C to 125°C	120			dB
A <sub>OL</sub>	Open-loop voltage gain	$(V-) + 0.6 V < V_0 < (V+) - 0.6 V$	T <sub>A</sub> = 25°C	114	120		uБ
			$T_A = -40$ °C to 125°C	110			
FREQUEN	NCY RESPONSE						
GBW	Gain bandwidth product				18		MHz
SR	Slew rate				6.4		V/µs
Φт	Phase margin	$R_L = 10 \text{ k}\Omega, C_L = 25 \text{ pF}$			80		٥
A Cottling time	$0.1\%$ , G = $-1$ , 10-V step, $C_L = 100$	) pF		2.1			
t <sub>S</sub> Settling time		0.0015% (16-bit), G = -1, 10-V ste	ep, C <sub>L</sub> = 100 pF	2.6			μs
	Overload recovery time	G = -1		< 1			μs
THD+N	Total harmonic distortion + noise	$G = +1$ , $f = 1$ kHz, $V_O = 20$ $V_{PP}$ , $60$	00 Ω	0.000025%			
OUTPUT							
		$R_L = 10 \text{ k}\Omega, A_{OL} > 130 \text{ dB}$		(V-) + 0.2	-	(V+) - 0.2	
	Voltage output swing	$R_L = 600 \ \Omega, \ A_{OL} > 114 \ dB$		(V-) + 0.6	-	(V+) - 0.6	V
		$R_L = 10 \text{ k}\Omega, A_{OL} > 120 \text{ dB}, T_A = -4$	40°C to 125°C	(V-) + 0.2	-	(V+) - 0.2	
I <sub>SC</sub>	Short-circuit current	V <sub>S</sub> = ±18 V			±65		mA
$C_{LOAD}$	Capacitive load drive (stable operation)			See Typical	l Characteris	tics	
Z <sub>O</sub>	Open-loop output impedance			See Typical Characteristics			
POWER S	SUPPLY					,	
	Quiescent current	Ι - 0 Δ	T <sub>A</sub> = 25°C		2.2	2.5	m 1
IQ	(per amplifier)	I <sub>O</sub> = 0 A	$T_A = -40^{\circ}C$ to 125°C	3.25			mA

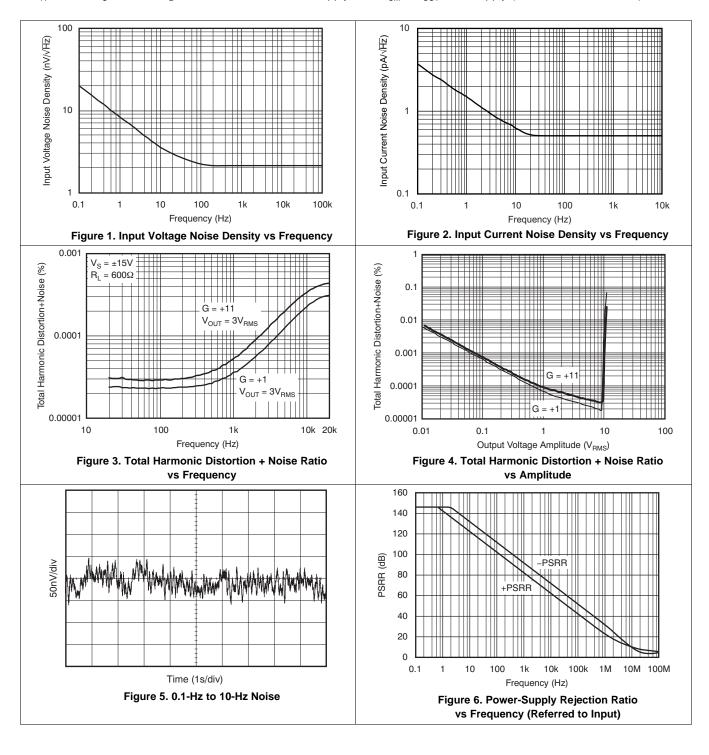
<sup>(1)</sup> See Absolute Maximum Ratings for additional information.

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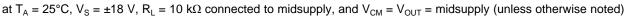
## 6.8 Typical Characteristics

at  $T_A = 25$ °C,  $V_S = \pm 18$  V,  $R_L = 10$  k $\Omega$  connected to midsupply, and  $V_{CM} = V_{OUT} =$  midsupply (unless otherwise noted)





## **Typical Characteristics (continued)**



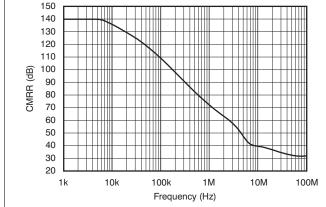


Figure 7. Common-Mode Rejection Ratio vs Frequency

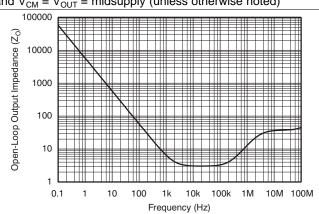


Figure 8. Open-Loop Output Impedance vs Frequency

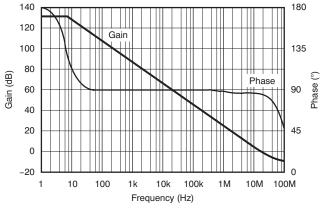


Figure 9. Open-Loop Gain and Phase vs Frequency

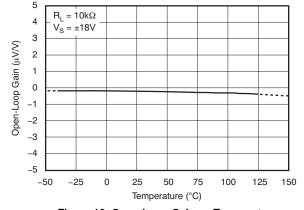
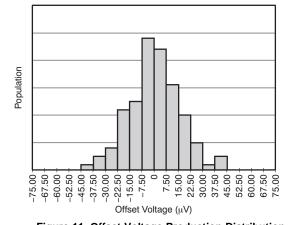


Figure 10. Open-Loop Gain vs Temperature





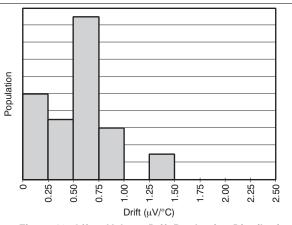


Figure 12. Offset Voltage Drift Production Distribution

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## **Typical Characteristics (continued)**

at  $T_A = 25$ °C,  $V_S = \pm 18$  V,  $R_L = 10$  k $\Omega$  connected to midsupply, and  $V_{CM} = V_{OUT} =$  midsupply (unless otherwise noted)

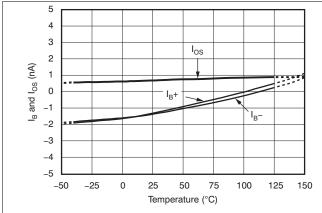


Figure 13. Input Bias and Input Offset Currents vs Temperature

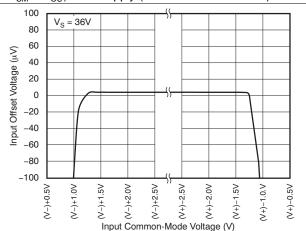


Figure 14. Input Offset Voltage vs Common-Mode Voltage

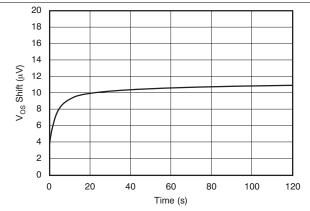


Figure 15. Input Offset Voltage vs Time

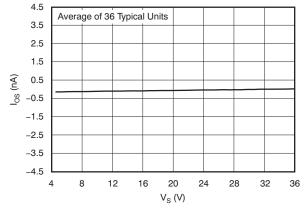


Figure 16. Input Offset Current vs Supply Voltage

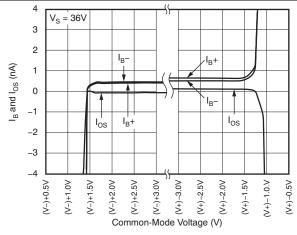


Figure 17. Input Bias and Input Offset Currents vs Common-Mode Voltage

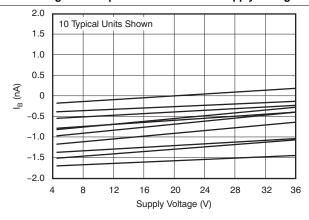


Figure 18. Input Bias Current vs Supply Voltage

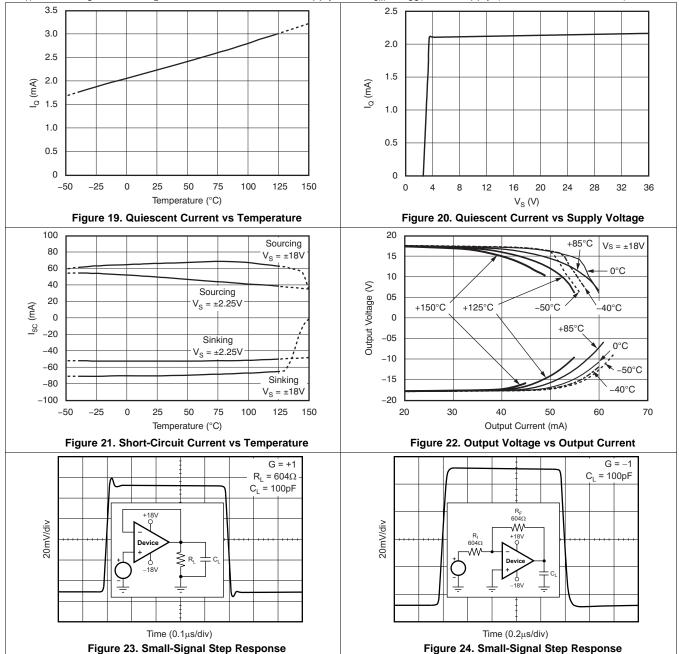
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## **Typical Characteristics (continued)**

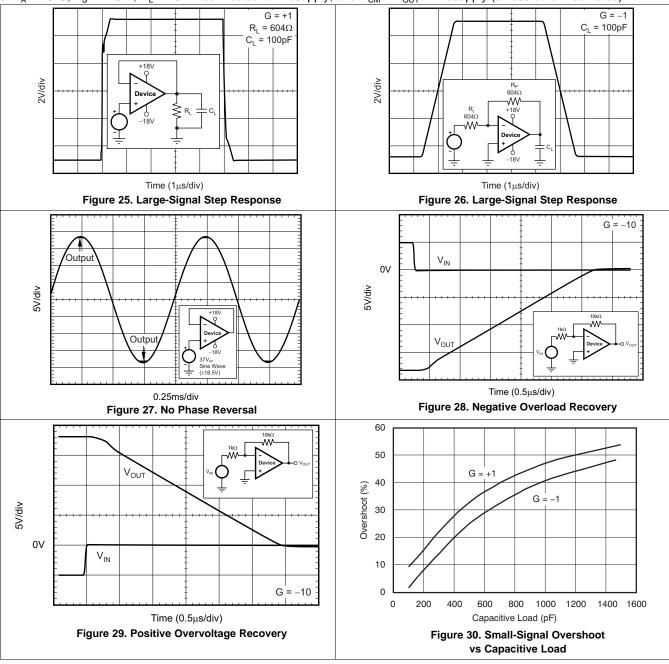
at  $T_A = 25$ °C,  $V_S = \pm 18$  V,  $R_L = 10$  k $\Omega$  connected to midsupply, and  $V_{CM} = V_{OUT} =$  midsupply (unless otherwise noted)





## **Typical Characteristics (continued)**

at  $T_A = 25$ °C,  $V_S = \pm 18$  V,  $R_L = 10$  k $\Omega$  connected to midsupply, and  $V_{CM} = V_{OUT} =$  midsupply (unless otherwise noted)



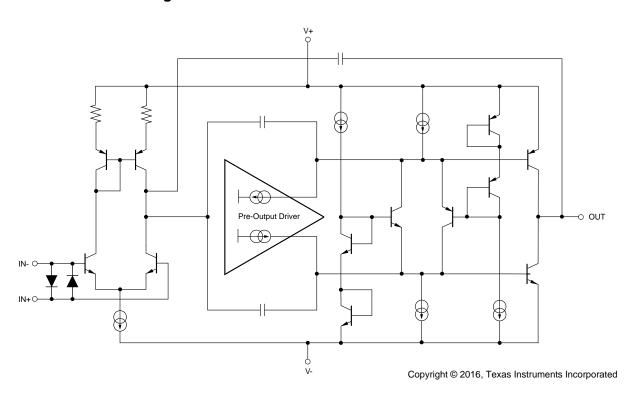


## 7 Detailed Description

#### 7.1 Overview

The OPA209 series of precision operational amplifiers are unity-gain stable, and free from unexpected output and phase reversal. Applications with noisy or high-impedance power supplies require decoupling capacitors placed close to the device pins. In most cases, 0.1-µF capacitors are adequate. The *Functional Block Diagram* shows a simplified schematic of the OPA209. This die uses a SiGe bipolar process and contains 180 transistors.

## 7.2 Functional Block Diagram



## 7.3 Feature Description

#### 7.3.1 Operating Voltage

The OPA209 series of op amps can be used with single or dual supplies within an operating range of  $V_S = 4.5 \text{ V}$  (±2.25 V) up to 36 V (±18 V). Supply voltages higher than 40 V total can permanently damage the device (see *Absolute Maximum Ratings*).

In addition, key parameters are assured over the specified temperature range,  $T_A = -40$ °C to 125°C. Parameters that vary significantly with operating voltage or temperature are shown in the *Typical Characteristics*.

#### 7.3.2 Input Protection

The input terminals of the OPA209 are protected from excessive differential voltage with back-to-back diodes, as shown in Figure 31. In most circuit applications, the input protection circuitry has no consequence. However, in low-gain or G = 1 circuits, fast ramping input signals can forward-bias these diodes because the output of the amplifier cannot respond rapidly enough to the input ramp. This effect is illustrated in Figure 25 and Figure 26 in *Typical Characteristics*. If the input signal is fast enough to create this forward-bias condition, the input signal current must be limited to 10 mA or less. If the input signal current is not inherently limited, an input series resistor can be used to limit the signal input current. This input series resistor degrades the low-noise performance of the OPA209. See *Noise Performance* for further information on noise performance.

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Figure 31 shows an example configuration that implements a current-limiting feedback resistor.

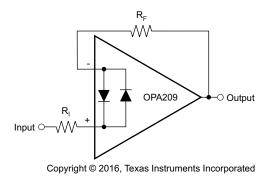


Figure 31. Pulsed Operation

#### 7.3.3 Noise Performance

Figure 32 shows the total circuit noise for varying source impedances with the op amp in a unity-gain configuration (no feedback resistor network, and therefore no additional noise contributions). Two different op amps are shown with the total circuit noise calculated. The OPA209 has very low voltage noise, making it ideal for low source impedances (less than 2 k $\Omega$ ). As a comparable precision FET-input op amp (very low current noise), the OPA827 has somewhat higher voltage noise, but lower current noise. It provides excellent noise performance at moderate to high source impedance (10 k $\Omega$  and up). For source impedance lower than 300  $\Omega$ , the OPA211 may provide lower noise.

The equation in Figure 32 shows the calculation of the total circuit noise, with these parameters:

- e<sub>n</sub> = voltage noise,
- i<sub>n</sub> = current noise,
- R<sub>S</sub> = source impedance,
- $k = Boltzmann's constant = 1.38 \times 10^{-23} J/K$ , and
- T = temperature in Kelvins

For more details on calculating noise, see Basic Noise Calculations.

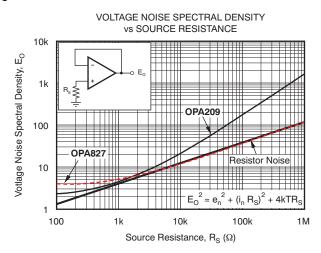


Figure 32. Noise Performance of the OPA209 and OPA827 in Unity-Gain Buffer Configuration



#### 7.3.4 Basic Noise Calculations

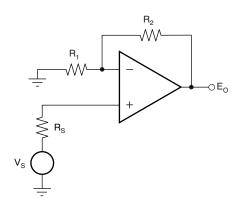
Low-noise circuit design requires careful analysis of all noise sources. External noise sources can dominate in many cases; consider the effect of source resistance on overall op amp noise performance. Total noise of the circuit is the root-sum-square combinations of all noise components.

The resistive portion of the source impedance produces thermal noise proportional to the square root of the resistance. This function is illustrated in Figure 32. The source impedance is usually fixed; consequently, select the appropriate op amp and the feedback resistors to minimize the respective contributions to the total noise.

Figure 33 illustrates both noninverting (Figure 33a) and inverting (Figure 33b) op amp circuit configurations with gain. In circuit configurations with gain, the feedback network resistors also contribute noise. The current noise of the op amp reacts with the feedback resistors to create additional noise components.

The feedback resistor values can generally be chosen to make these noise sources negligible. Note that low-impedance feedback resistors load the output of the amplifier. The equations for total noise are shown for both configurations.

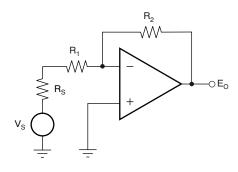
#### A) Noise in Noninverting Gain Configuration



Noise at the output:

$$\begin{split} E_{O}^{\ 2} &= \left(1 + \frac{R_{2}}{R_{1}}\right)^{2} \, e_{n}^{\ 2} + e_{1}^{\ 2} + e_{2}^{\ 2} + (i_{n}^{\ }R_{2})^{2} + e_{S}^{\ 2} + (i_{n}^{\ }R_{S})^{2} \left(1 + \frac{R_{2}}{R_{1}}\right)^{2} \end{split}$$
 Where  $e_{S} = \sqrt{4kTR_{S}} \times \left(1 + \frac{R_{2}}{R_{1}}\right) = \text{thermal noise of } R_{S}$  
$$e_{1} = \sqrt{4kTR_{1}} \times \left(\frac{R_{2}}{R_{1}}\right) = \text{thermal noise of } R_{1}$$
 
$$e_{2} = \sqrt{4kTR_{2}} = \text{thermal noise of } R_{2}$$

#### B) Noise in Inverting Gain Configuration



Noise at the output:

$$E_{O}^{2} = \left(1 + \frac{R_{2}}{R_{1} + R_{S}}\right)^{2} e_{n}^{2} + e_{1}^{2} + e_{2}^{2} + (i_{n}R_{2})^{2} + e_{S}^{2}$$
Where  $e_{S} = \sqrt{4kTR_{S}} \times \left(\frac{R_{2}}{R_{1} + R_{S}}\right)$  = thermal noise of  $R_{S}$ 

$$e_{1} = \sqrt{4kTR_{1}} \times \left(\frac{R_{2}}{R_{1} + R_{S}}\right)$$
 = thermal noise of  $R_{1}$ 

$$e_{2} = \sqrt{4kTR_{2}}$$
 = thermal noise of  $R_{2}$ 

For the OPA209 series op amps at 1 kHz,  $e_n = 2.2 \text{ nV/}\sqrt{\text{Hz}}$  and  $I_n = 530 \text{ fA/}\sqrt{\text{Hz}}$ .

Figure 33. Noise Calculation in Gain Configurations



#### 7.3.5 Electrical Overstress

Designers often ask questions about the capability of an operational amplifier to withstand electrical overstress. These questions tend to focus on the device inputs, but may involve the supply voltage pins or even the output pin. Each of these different pin functions have electrical stress limits determined by the voltage breakdown characteristics of the particular semiconductor fabrication process and specific circuits connected to the pin. Additionally, internal electrostatic discharge (ESD) protection is built into these circuits to protect them from accidental ESD events both before and during product assembly.

It is helpful to have a good understanding of this basic ESD circuitry and its relevance to an electrical overstress event. See Figure 34 for an illustration of the ESD circuits contained in the OPA209 series (indicated by the dashed line area). The ESD protection circuitry involves several current-steering diodes connected from the input and output pins and routed back to the internal power-supply lines, where they meet at an absorption device internal to the operational amplifier. This protection circuitry is intended to remain inactive during normal circuit operation.

An ESD event produces a short duration, high-voltage pulse that is transformed into a short duration, high-current pulse as it discharges through a semiconductor device. The ESD protection circuits are designed to provide a current path around the operational amplifier core to prevent it from being damaged. The energy absorbed by the protection circuitry is then dissipated as heat.

When an ESD voltage develops across two or more of the amplifier device pins, current flows through one or more of the steering diodes. Depending on the path that the current takes, the absorption device may activate. The absorption device has a trigger, or threshold voltage, that is above the normal operating voltage of the OPA209 but below the device breakdown voltage level. Once this threshold is exceeded, the absorption device quickly activates and clamps the voltage across the supply rails to a safe level.

When the operational amplifier connects into a circuit such as the one Figure 34 shows, the ESD protection components are intended to remain inactive and not become involved in the application circuit operation. However, circumstances may arise where an applied voltage exceeds the operating voltage range of a given pin. If this condition occur, there is a risk that some of the internal ESD protection circuits may be biased on, and conduct current. Any such current flow occurs through steering diode paths and rarely involves the absorption device.

Figure 34 depicts a specific example where the input voltage,  $V_{IN}$ , exceeds the positive supply voltage (+V<sub>S</sub>) by 500 mV or more. Much of what happens in the circuit depends on the supply characteristics. If +V<sub>S</sub> can sink the current, one of the upper input steering diodes conducts and directs current to +V<sub>S</sub>. Excessively high current levels can flow with increasingly higher  $V_{IN}$ . As a result, the datasheet specifications recommend that applications limit the input current to 10 mA.

If the supply is not capable of sinking the current,  $V_{IN}$  may begin sourcing current to the operational amplifier, and then take over as the source of positive supply voltage. The danger in this case is that the voltage can rise to levels that exceed the operational amplifier absolute maximum ratings.

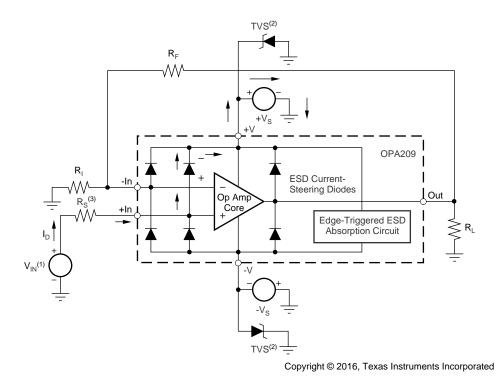
Another common question involves what happens to the amplifier if an input signal is applied to the input while the power supplies  $+V_S$  and/or  $-V_S$  are at 0 V.

Again, it depends on the supply characteristic while at 0 V, or at a level below the input signal amplitude. If the supplies appear as high impedance, then the operational amplifier supply current may be supplied by the input source through the current steering diodes. This state is not a normal bias condition; the amplifier will not operate normally. If the supplies are low impedance, then the current through the steering diodes can become quite high. The current level depends on the ability of the input source to deliver current, and any resistance in the input path.

If there is an uncertainty about the ability of the supply to absorb this current, external Zener diodes may be added to the supply pins as shown in Figure 34. The Zener voltage must be selected such that the diode does not turn on during normal operation.

However, its Zener voltage must be low enough so that the Zener diode conducts if the supply pin begins to rise above the safe operating supply voltage level.





- (1)  $V_{IN} = +V_S + 500 \text{ mV}$
- (2) TVS:  $+V_{S(max)} > V_{TVSBR (Min)} > +V_{S}$
- (3) Suggested value approximately 1  $k\Omega$

Figure 34. Equivalent Internal ESD Circuitry and Its Relation to a Typical Circuit Application

## 7.4 Device Functional Modes

The OPAx209 is operational when the power-supply voltage is greater than 4.5 V (±2.25 V). The maximum power-supply voltage for the OPAx209 is 36 V (±18 V).

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## 8 Application and Implementation

#### NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

## 8.1 Application Information

The OPAx209 are unity-gain stable, precision operational amplifiers with very low noise. Applications with noisy or high-impedance power supplies require decoupling capacitors close to the device pins. In most cases, 0.1-µF capacitors are adequate.

## 8.2 Typical Application

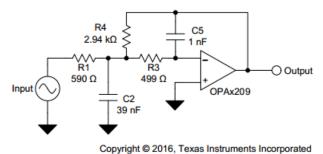


Figure 35. Low-Pass Filter

#### 8.2.1 Design Requirements

Low-pass filters are commonly employed in signal processing applications to reduce noise and prevent aliasing. The OPAx209 are ideally suited to construct high-speed, high-precision active filters. Figure 35 shows a second-order, low-pass filter commonly encountered in signal processing applications.

Use the following parameters for this design example:

- Gain = 5 V/V (inverting gain)
- Low-pass cutoff frequency = 25 kHz
- Second-order Chebyshev filter response with 3-dB gain peaking in the passband

## 8.2.2 Detailed Design Procedure

The infinite-gain multiple-feedback circuit for a low-pass network function is shown in Figure 35. Use Equation 1 to calculate the voltage transfer function.

$$\frac{\text{Output}}{\text{Input}}(s) = \frac{-1/R_1R_3C_2C_5}{s^2 + (s/C_2)(1/R_1 + 1/R_3 + 1/R_4) + 1/R_3R_4C_2C_5}$$
(1)

This circuit produces a signal inversion. For this circuit, the gain at DC and the low-pass cutoff frequency are calculated by Equation 2:

Gain = 
$$\frac{R_4}{R_1}$$
  
 $f_c = \frac{1}{2\pi} \sqrt{(1/R_3 R_4 C_2 C_5)}$  (2)



## **Typical Application (continued)**

## 8.2.3 Application Curve

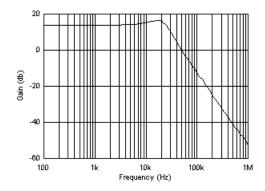


Figure 36. OPAx209 Second-Order, 25-kHz, Chebyshev, Low-Pass Filter

## 9 Power Supply Recommendations

The OPAx209 is specified for operation from 4.5 V to 36 V (±2.25 V to ±18 V); many specifications apply from –40°C to 125°C. Parameters that can exhibit significant variance with regard to operating voltage or temperature are presented in the *Typical Characteristics*.

## 10 Layout

## 10.1 Layout Guidelines

For best operational performance of the device, use good printed circuit board (PCB) layout practices, including the following guidelines:

- Noise can propagate into analog circuitry through the power pins of the circuit as a whole and op amp itself.
   Bypass capacitors are used to reduce the coupled noise by providing low-impedance power sources local to the analog circuitry.
- Connect low-ESR, 0.1-µF ceramic bypass capacitors between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V+ to ground is applicable for single-supply applications.
- Separate grounding for analog and digital portions of circuitry is one of the simplest and most-effective
  methods of noise suppression. One or more layers on multilayer PCBs are usually devoted to ground planes.
  A ground plane helps distribute heat and reduces EMI noise pickup. Make sure to physically separate digital
  and analog grounds paying attention to the flow of the ground current.
- To reduce parasitic coupling, run the input traces as far away from the supply or output traces as possible. If these traces cannot be kept separate, crossing the sensitive trace perpendicular is much better as opposed to in parallel with the noisy trace.
- Place the external components as close to the device as possible.
- Keep the length of input traces as short as possible. Always remember that the input traces are the most sensitive part of the circuit.
- Consider a driven, low-impedance guard ring around the critical traces. A guard ring can significantly reduce leakage currents from nearby traces that are at different potentials.
- Cleaning the PCB following board assembly is recommended for best performance.
- Any precision integrated circuit may experience performance shifts due to moisture ingress into the plastic package. Following any aqueous PCB cleaning process, baking the PCB assembly is recommended to remove moisture introduced into the device packaging during the cleaning process. A low-temperature, postcleaning bake at 85°C for 30 minutes is sufficient for most circumstances.

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## 10.2 Layout Example

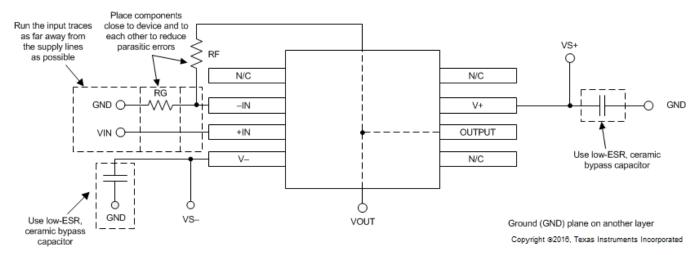


Figure 37. OPAx209 Layout Example



## 11 Device and Documentation Support

## 11.1 Device Support

#### 11.1.1 Development Support

#### 11.1.1.1 TINA-TI™ (Free Software Download)

TINA<sup>TM</sup> is a simple, powerful, and easy-to-use circuit simulation program based on a SPICE engine. TINA-TI<sup>TM</sup> is a free, fully-functional version of the TINA software, preloaded with a library of macro models in addition to a range of both passive and active models. TINA-TI provides all the conventional DC, transient, and frequency domain analysis of SPICE, as well as additional design capabilities.

Available as a free download from the Analog eLab Design Center, TINA-TI offers extensive post-processing capability that allows users to format results in a variety of ways. Virtual instruments offer the ability to select input waveforms and probe circuit nodes, voltages, and waveforms, creating a dynamic quick-start tool.

#### NOTE

These files require that either the TINA software (from DesignSoft™) or TINA-TI software be installed. Download the free TINA-TI software from the TINA-TI folder.

## 11.1.1.2 DIP Adapter EVM

The DIP Adapter EVM tool provides an easy, low-cost way to prototype small surface mount ICs. The evaluation tool these TI packages: D or U (SOIC-8), PW (TSSOP-8), DGK (VSSOP-8), DBV (SOT23-6, SOT23-5 and SOT23-3), DCK (SC70-6 and SC70-5), and DRL (SOT563-6). The DIP Adapter EVM may also be used with terminal strips or may be wired directly to existing circuits.

## 11.1.1.3 Universal Operational Amplifier EVM

The Universal Op Amp EVM is a series of general-purpose, blank circuit boards that simplify prototyping circuits for a variety of IC package types. The evaluation module board design allows many different circuits to be constructed easily and quickly. Five models are offered, with each model intended for a specific package type. PDIP, SOIC, VSSOP, TSSOP, and SOT-23 packages are all supported.

## **NOTE**

These boards are unpopulated, so users must provide their own ICs. TI recommends requesting several op amp device samples when ordering the Universal Op Amp EVM.

## 11.1.1.4 TI Precision Designs

TI Precision Designs are analog solutions created by Ti's precision analog applications experts and offer the theory of operation, component selection, simulation, complete PCB schematic and layout, bill of materials, and measured performance of many useful circuits. TI Precision Designs are available online at <a href="http://www.ti.com/ww/en/analog/precision-designs/">http://www.ti.com/ww/en/analog/precision-designs/</a>.

## 11.1.1.5 WEBENCH® Filter Designer

WEBENCH® Filter Designer is a simple, powerful, and easy-to-use active filter design program. The WEBENCH Filter Designer lets you create optimized filter designs using a selection of TI operational amplifiers and passive components from TI's vendor partners.

Available as a web-based tool from the WEBENCH® Design Center, WEBENCH® Filter Designer allows you to design, optimize, and simulate complete multistage active filter solutions within minutes.

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## 11.2 Documentation Support

#### 11.2.1 Related Documentation

The following documents are relevant to using the OPAx209 and recommended for reference. All are available for download at www.ti.com (unless otherwise noted):

- OPA827 Low-Noise, High-Precision, JFET-Input Operational Amplifier (SBOS376)
- OPA2x11 1.1-nv√Hz Noise, Low Power, Precision Operational Amplifier (SBOS377)
- OPA209, OPA2209, OPA4209 EMI Immunity Performance (SBOZ020)
- Microcontroller PWM to 12-bit Analog Out (TIDU027)
- Capacitive Load Drive Solution Using an Isolation Resistor (TIDU032)
- Noise Measurement Post Amp (TIDU016)
- Diagnostic Patient Monitoring and Therapy Guide (SLYB147)

#### 11.3 Related Links

Table 1 lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

Table 1. Related Links

PARTS	PRODUCT FOLDER	SAMPLE & BUY	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY
OPA209	Click here	Click here	Click here	Click here	Click here
OPA2209	Click here	Click here	Click here	Click here	Click here
OPA4209	Click here	Click here	Click here	Click here	Click here

## 11.4 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

## 11.5 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community T's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

**Design Support** *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

#### 11.6 Trademarks

TINA-TI, E2E are trademarks of Texas Instruments.

WEBENCH is a registered trademark of Texas Instruments.

TINA, DesignSoft are trademarks of DesignSoft, Inc.

All other trademarks are the property of their respective owners.

## 11.7 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

Product Folder Links: OPA209 OPA2209 OPA4209



## 11.8 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

# 12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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#### **PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
OPA209AID	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	OPA 209A	Samples
OPA209AIDBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	OOBQ	Samples
OPA209AIDBVT	ACTIVE	SOT-23	DBV	5	250	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	OOBQ	Samples
OPA209AIDGKR	ACTIVE	VSSOP	DGK	8	2500	RoHS & Green	NIPDAU   NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	OOAQ	Samples
OPA209AIDGKT	ACTIVE	VSSOP	DGK	8	250	RoHS & Green	NIPDAU   NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	OOAQ	Samples
OPA209AIDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	OPA 209A	Samples
OPA2209AID	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	O2209	Samples
OPA2209AIDGKR	ACTIVE	VSSOP	DGK	8	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	OOJI	Samples
OPA2209AIDGKT	ACTIVE	VSSOP	DGK	8	250	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	OOJI	Samples
OPA2209AIDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	O2209	Samples
OPA4209AIPW	ACTIVE	TSSOP	PW	14	90	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	(OP4209A, OPA) 4209	Samples
OPA4209AIPWR	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	(OP4209A, OPA) 4209	Samples

<sup>(1)</sup> The marketing status values are defined as follows: **ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

<sup>(2)</sup> RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".



## PACKAGE OPTION ADDENDUM

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- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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## TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

## QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
OPA209AIDBVR	SOT-23	DBV	5	3000	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
OPA209AIDBVR	SOT-23	DBV	5	3000	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
OPA209AIDBVT	SOT-23	DBV	5	250	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
OPA209AIDBVT	SOT-23	DBV	5	250	179.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
OPA209AIDGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
OPA209AIDGKT	VSSOP	DGK	8	250	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
OPA209AIDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
OPA2209AIDGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
OPA2209AIDGKT	VSSOP	DGK	8	250	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
OPA2209AIDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
OPA4209AIPWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1



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\*All dimensions are nominal

All difficultions are norminal							
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
OPA209AIDBVR	SOT-23	DBV	5	3000	223.0	270.0	35.0
OPA209AIDBVR	SOT-23	DBV	5	3000	190.0	190.0	30.0
OPA209AIDBVT	SOT-23	DBV	5	250	223.0	270.0	35.0
OPA209AIDBVT	SOT-23	DBV	5	250	213.0	191.0	35.0
OPA209AIDGKR	VSSOP	DGK	8	2500	356.0	356.0	35.0
OPA209AIDGKT	VSSOP	DGK	8	250	356.0	356.0	35.0
OPA209AIDR	SOIC	D	8	2500	356.0	356.0	35.0
OPA2209AIDGKR	VSSOP	DGK	8	2500	356.0	356.0	35.0
OPA2209AIDGKT	VSSOP	DGK	8	250	356.0	356.0	35.0
OPA2209AIDR	SOIC	D	8	2500	356.0	356.0	35.0
OPA4209AIPWR	TSSOP	PW	14	2000	356.0	356.0	35.0

# **PACKAGE MATERIALS INFORMATION**

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## **TUBE**



\*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
OPA209AID	D	SOIC	8	75	506.6	8	3940	4.32
OPA2209AID	D	SOIC	8	75	506.6	8	3940	4.32
OPA4209AIPW	PW	TSSOP	14	90	530	10.2	3600	3.5



SMALL OUTLINE INTEGRATED CIRCUIT



## NOTES:

- 1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.
- 5. Reference JEDEC registration MS-012, variation AA.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE INTEGRATED CIRCUIT



#### NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.







## NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.





NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.





SMALL OUTLINE TRANSISTOR



## NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
  2. This drawing is subject to change without notice.
  3. Reference JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
- 5. Support pin may differ or may not be present.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.







## NOTES:

PowerPAD is a trademark of Texas Instruments.

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-187.





NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
- 8. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.
- 9. Size of metal pad may vary due to creepage requirement.





NOTES: (continued)

- 11. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 12. Board assembly site may have different recommendations for stencil design.



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